

**IN THE SPECIFICATION:**

Please replace the paragraph beginning on page 5, line 1, with the following rewritten paragraph:

The main difficulty in obtaining high accuracy in optical EPD is signal dependency on wafer pattern, since EPD spot size includes a lot of features with different layers structure. The effect may be stronger than signal change during polishing. There is a great variety of approaches aimed at increasing the accuracy of the endpoint detection. US Patent No. ~~5,910,001~~5,910,011 discloses a method and apparatus for in-situ monitoring, using multiple process parameters. This technique utilizes analyses of the multiple process parameters and statistical correlation of these parameters to detect changes in process characteristics, such that the endpoint of the etching process may be accurately detected. Another improved endpoint technique is disclosed in US Patent No. 5,964,980. Here, a fitted endpoint system provides normalizing the current endpoint curve generated from the series of multi-bit digital code words for a wafer being etched with respect to the standard endpoint curve and providing a normalized current endpoint curve.

The Examiner has determined that the claims in the present invention contain two separate species:

Group I – claims 26-33, 36-42 and 45 related to a CVD process and apparatus;  
and

Group II – claims 26-31, 34-40, 43-44 and 46 related to an etching process and apparatus.

The Examiner has required Applicant to elect a single disclosed species for prosecution on the merits. Applicant elects without traverse the species of Group II, relating to an etching process and apparatus. Applicant acknowledges the Examiner's indication that claims 26-31 and 36-40 are generic. Applicant submits that claims 26-31, 34-40, 43-44 and 46 relate to the invention of species in Group II. Applicant recognizes that upon allowance of a generic claim, this requirement will be withdrawn.